

Title (en)

USE OF SURFACTANT/DEFOAMER MIXTURES FOR ENHANCED METALS LOADING AND SURFACE PASSIVATION OF SILICON SUBSTRATES

Title (de)

VERWENDUNG VON TENSID-/ENTSCHÄUMUNGSMISCHUNGEN FÜR ERHÖHTE METALLLADUNG UND OBERFLÄCHENPASSIVIERUNG VON SILIZIUMSUBSTRATEN

Title (fr)

EMPLOI DE MELANGES TENSIOACTIF/AGENT ANTIMOUSSE POUR AMELIORER LA CHARGE METALLIQUE ET LA PASSIVATION DE SURFACE DE SUBSTRATS DE SILICIUM

Publication

EP 2342738 A4 20130417 (EN)

Application

EP 09818502 A 20091001

Priority

- US 2009059199 W 20091001
- US 10235208 P 20081002
- US 14498609 P 20090115

Abstract (en)

[origin: WO2010039936A2] Removal compositions and processes for removing at least one material layer from a rejected microelectronic device structure having same thereon. The removal composition includes hydrofluoric acid. The composition achieves substantial removal of the material(s) to be removed while not damaging the layers to be retained, for reclaiming, reworking, recycling and / or reuse of said structure.

IPC 8 full level

C09K 13/08 (2006.01); **C23F 1/18** (2006.01); **H01L 21/311** (2006.01); **H01L 21/3213** (2006.01)

CPC (source: EP KR)

C09K 13/08 (2013.01 - EP KR); **C11D 1/00** (2013.01 - EP); **C11D 1/008** (2013.01 - EP KR); **C11D 1/72** (2013.01 - EP KR); **C11D 1/78** (2013.01 - EP KR); **C11D 3/0026** (2013.01 - EP KR); **C11D 3/042** (2013.01 - EP); **C11D 3/2068** (2013.01 - EP KR); **C11D 3/37** (2013.01 - EP); **C11D 3/3707** (2013.01 - EP KR); **C23F 1/18** (2013.01 - EP KR); **H01L 21/02032** (2013.01 - EP KR); **H01L 21/31111** (2013.01 - EP); **H01L 21/32134** (2013.01 - EP KR); **C11D 2111/22** (2024.01 - EP KR)

Citation (search report)

- [I] EP 1975987 A2 20081001 - ADVANCED TECH MATERIALS [US]
- [A] US 2004018453 A1 20040129 - ANZURES EDGARDO [US], et al

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK SM TR

DOCDB simple family (publication)

WO 2010039936 A2 20100408; **WO 2010039936 A3 20100701**; CN 102217042 A 20111012; EP 2342738 A2 20110713; EP 2342738 A4 20130417; JP 2012504871 A 20120223; KR 20110063845 A 20110614; TW 201022148 A 20100616; TW I485110 B 20150521

DOCDB simple family (application)

US 2009059199 W 20091001; CN 200980146332 A 20091001; EP 09818502 A 20091001; JP 2011530216 A 20091001; KR 20117009703 A 20091001; TW 98133617 A 20091002